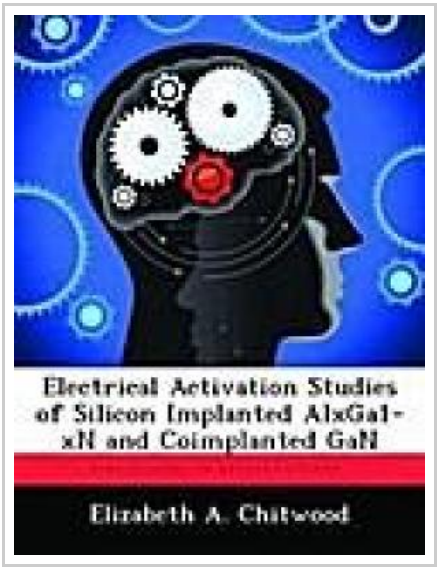

Electrical Activation Studies of Silicon Implanted AlxGa1-xN and Coimplanted GaN

By Elizabeth A. Chitwood

Bibliioscholar Okt 2012, 2012. Taschenbuch. Book Condition: Neu. 246x189x5 mm. This item is printed on demand - Print on Demand Neuware - A comprehensive study of the electrical activation of silicon implanted AlxGa1-xN was performed as a function ion dose, anneal temperature, and aluminum mole fraction. Also, GaN coimplanted with silicon and nitrogen was investigated. Room temperature Hall effect measurements were used to determine carrier concentration and mobility. All the samples had a 500 Å encapsulant of AlN, and were implanted at room temperature with 200 keV silicon ions at doses ranging from 1x1013 to 1x1015 cm-2. The GaN was also implanted with nitrogen under the same conditions in doses of 9x1012 to 9x1014 cm-2, respectively. The samples were annealed at temperatures ranging from 1200 to 1350 oC for 30 to 120 seconds in a flowing nitrogen environment. 78 pp. Englisch.

Reviews

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